# EMH3 / UMH3N / IMH3A

NPN 100mA 50V Complex Digital Transistors (Bias Resistor Built-in Transistors)

Datasheet

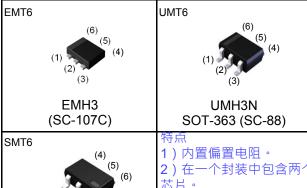
Parameter	Tr1 and Tr2
$V_{CEO}$	50V
I <sub>C(MAX.)</sub>	100mA
R <sub>1</sub>	4.7kΩ

#### Features

- 1) Built-In Biasing Resistors.
- 2) Two DTC143T chips in one package.
- 3) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit).
- 4) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- 5) Only the on/off conditions need to be set for operation, making the circuit design easy.
- 6) Lead Free/RoHS Compliant.

#### Application

#### Outline



IMH3A

SOT-457 (SC-74)

●Inner circuit

Collecto

(1)

Emitter

EMH3 / UMH3N

Base

(5)

(2)

Emitter

(4)

(3)

Collector

2)在一个封装中包含两个DTC143T

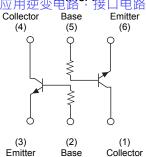
3)内置偏置电阻器无需连接外部输 入电阻器即可配置逆变器电路(请参 阅内部电路)

4)偏置电阻由完全隔离的薄膜电阻 组成,可实现负偏置

输入的它们还具有完全消除寄生效应 的优势。

5) 只需设置开/关条件即可操作,使 电路设计变得容易

6) 无铅/符合RoHS 应用逆变 接口电路,驱动电路



Inverter circuit, Interface circuit, Driver circuit

#### Packaging specifications

-1 dokaging opcomodulone							
Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
EMH3	EMT6	1616	T2R	180	8	8,000	H3
UMH3N	UMT6	2021	TN	180	8	3,000	H3
IMH3A	SMT6	2928	T110	180	8	3,000	H3

#### ● Absolute maximum ratings (Ta = 25°C)

<For Tr1 and Tr2 in common>

Paramete	Symbol	Values	Unit	
Collector-base voltage	$V_{CBO}$	50	V	
Collector-emitter voltage	$V_{CEO}$	50	V	
Emitter-base voltage	$V_{EBO}$	5	V	
Collector current		I <sub>C(MAX.)</sub> *1	100	mA
Collector Power dissipation EMH3 / UMH3N		P <sub>D</sub> *2	150 (Total) <sup>*3</sup>	mW
IMH3A			300 (Total) <sup>*4</sup>	mW
Junction temperature		T <sub>j</sub>	150	°C
Range of storage temperature		T <sub>stg</sub>	−55 to +150	°C

#### ●Electrical characteristics(Ta = 25°C)

<For Tr1 and Tr2 in common>

集电极

基极击穿甲	B压 Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
集电极-基	Collector-base breakdown voltage	$BV_CBO$	I <sub>C</sub> = 50μA	50	-	-	V
<b>发射极基</b> 标	Collector-emitter breakdown voltage	BV <sub>CEO</sub>	I <sub>C</sub> = 1mA	50	-	-	V
集电极截↓	Emitter-base breakdown voltage	$BV_{EBO}$	I <sub>E</sub> = 50μA	5	-	-	V
	Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 50V	-	-	0.5	μΑ
	Emitter cut-off current 財材饱和电压	I <sub>EBO</sub>	V <sub>EB</sub> = 4V	-	-	0.5	μΑ
	Collector-emitter saturation voltage	$V_{CE(sat)}$	I <sub>C</sub> / I <sub>B</sub> = 5mA / 0.25mA	-	-	0.15	V
	DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = 5V , I <sub>C</sub> = 1mA ,	100	250	600	-
	Input resistance	R <sub>1</sub>	-	3.5	4.7	5.9	kΩ
过渡频率 '	Transition frequency	f <sub>T</sub> *1	V <sub>CE</sub> = 10V, I <sub>E</sub> = -5mA, f = 100MHz	-	250	-	MHz

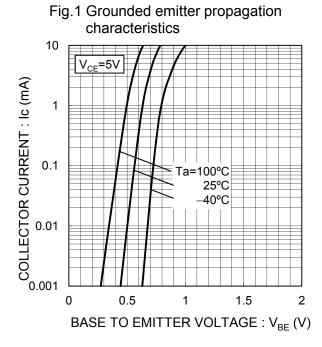
<sup>\*1</sup> Characteristics of built-in transistor

<sup>\*2</sup> Each terminal mounted on a reference footprint

<sup>\*3 120</sup>mW per element must not be exceeded.

<sup>\*4 200</sup>mW per element must not be exceeded.

#### ●Electrical characteristic curves(Ta = 25°C)



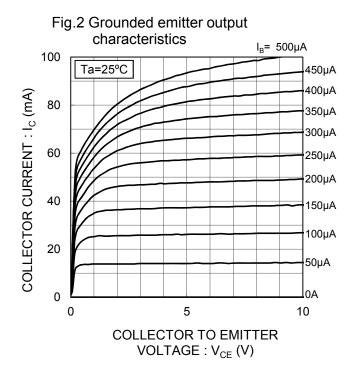
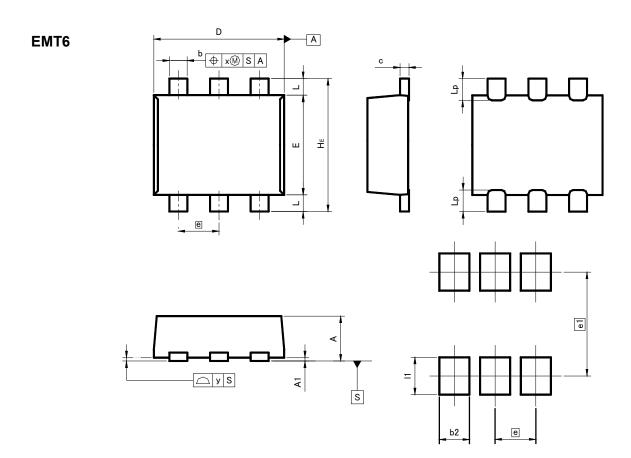


Fig.3 DC Current gain vs. Collector Current 1k V<sub>CE</sub>=5V 500 200 DC CURRENT GAIN: hFE Ta=100°C 100 25°C∰ 50 -40°C 20 10 5 2 100μ 200μ 500μ 1m 2m 5m 10m 20m 50m100m COLLECTOR CURRENT : I<sub>C</sub> (mA)

Fig.4 Collector-emitter saturation voltage vs. Collector Current  $I_C/I_B=20$ 500m **COLLECTOR SATURATION** 200m Ta=100°C VOLTAGE: V<sub>CE</sub>(sat) (V) 25°C 100m 50m 10m 5m 2m 5m 10m 20m COLLECTOR CURRENT :  $I_C$  (mA)

## ●Dimensions (Unit : mm)



#### Patterm of terminal position areas

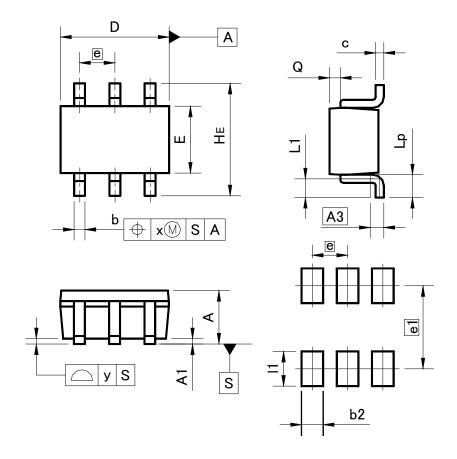
DIM	MILIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
A1	0.00	0.10	0	0.004
Α	0.45	0.55	0.018	0.022
b	0.17	0.27	0.007	0.011
С	0.08	0.18	0.003	0.007
D	1.50	1.70	0.059	0.067
Е	1.10	1.30	0.043	0.051
е	0.	50	0.02	
HE	1.50	1.70	0.059	0.067
L	0.10	0.30	0.004	0.012
Lp	_	0.35	_	0.014
х	_	0.10	_	0.004
٧	_	0.10	_	0.004

DIM	MILIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
e1	1.25		0.049		
b2	-	0.37	ı	0.015	
11	- 0.45			0.018	

Dimension in mm/inches

## ●Dimensions (Unit : mm)

#### UMT6



#### **Patterm of terminal position areas**

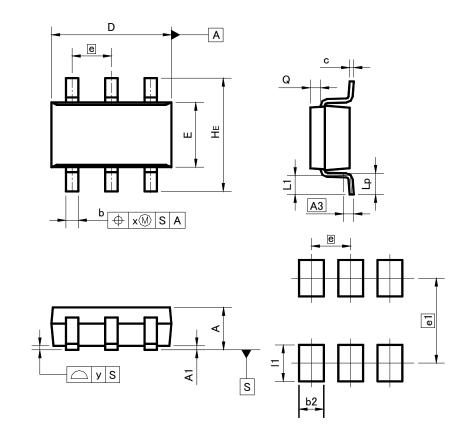
DIM	MILIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	0.80	1.00	1	0.039	
A1	0.00	0.10	0	0.004	
A3	0.2	25	0.0	01	
b	0.15	0.30	0.006	0.012	
С	0.10	0.20	0.004	0.008	
D	1.90	2.10	0.075	0.083	
E	1.15	1.35	0.045	0.053	
е	0.0	65	0.03		
HE	2.00	2.20	0.079	0.087	
L1	0.20	0.50	0.008	0.02	
Lp	0.25	0.55	0.01	0.022	
Q	0.10	0.30	0.004	0.012	
х	_	0.10	-	0.004	
У	_	0.10	-	0.004	

DIM	MILIMETERS		INCHES		
MIN		MAX	MIN	MAX	
e1	1.55		0.06		
b2	-	- 0.40		0.016	
11	- 0.65		-	0.026	

Dimension in mm/inches

## ●Dimensions (Unit : mm)

#### SMT6



#### Patterm of terminal position areas

DIM	MILIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	1.00	1.30	0.039	0.051	
A1	0.00	0.10	0	0.004	
A3	0.3	25	0.0	01	
b	0.25	0.40	0.01	0.016	
С	0.09	0.25	0.004	0.01	
D	2.80	3.00	0.11	0.118	
Е	1.50	1.80	0.059	0.071	
е	0.9	95	0.04		
HE	2.60	3.00	0.102	0.118	
L1	0.30	0.60	0.012	0.024	
Lp	0.40	0.70	0.016	0.028	
Q	0.20	0.30	0.008	0.012	
х	_	0.20	_	0.008	
У	_	0.10	_	0.004	

DIM	MILIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
e1	2.10		0.08		
b2		0.60	1	0.024	
11	-	0.90	ı	0.035	

Dimension in mm/inches

#### Notes

- 1) The information contained herein is subject to change without notice.
- Before you use our Products, please contact our sales representative and verify the latest specifications:
- 3) Although ROHM is continuously working to improve product reliability and quality, semiconductors can break down and malfunction due to various factors. Therefore, in order to prevent personal injury or fire arising from failure, please take safety measures such as complying with the derating characteristics, implementing redundant and fire prevention designs, and utilizing backups and fail-safe procedures. ROHM shall have no responsibility for any damages arising out of the use of our Poducts beyond the rating specified by ROHM
- 4) Examples of application circuits, circuit constants and any other information contained herein are provided only to illustrate the standard usage and operations of the Products. The peripheral conditions must be taken into account when designing circuits for mass production.
- 5) The technical information specified herein is intended only to show the typical functions of and examples of application circuits for the Products. ROHM does not grant you, explicitly or implicitly, any license to use or exercise intellectual property or other rights held by ROHM or any other parties. ROHM shall have no responsibility whatsoever for any dispute arising out of the use of such technical information.
- 6) The Products are intended for use in general electronic equipment (i.e. AV/OA devices, communication, consumer systems, gaming/entertainment sets) as well as the applications indicated in this document.
- 7) The Products specified in this document are not designed to be radiation tolerant.
- 8) For use of our Products in applications requiring a high degree of reliability (as exemplified below), please contact and consult with a ROHM representative: transportation equipment (i.e. cars, ships, trains), primary communication equipment, traffic lights, fire/crime prevention, safety equipment, medical systems, servers, solar cells, and power transmission systems.
- 9) Do not use our Products in applications requiring extremely high reliability, such as aerospace equipment, nuclear power control systems, and submarine repeaters.
- 10) ROHM shall have no responsibility for any damages or injury arising from non-compliance with the recommended usage conditions and specifications contained herein.
- 11) ROHM has used reasonable care to ensur the accuracy of the information contained in this document. However, ROHM does not warrants that such information is error-free, and ROHM shall have no responsibility for any damages arising from any inaccuracy or misprint of such information.
- 12) Please use the Products in accordance with any applicable environmental laws and regulations, such as the RoHS Directive. For more details, including RoHS compatibility, please contact a ROHM sales office. ROHM shall have no responsibility for any damages or losses resulting non-compliance with any applicable laws or regulations.
- 13) When providing our Products and technologies contained in this document to other countries, you must abide by the procedures and provisions stipulated in all applicable export laws and regulations, including without limitation the US Export Administration Regulations and the Foreign Exchange and Foreign Trade Act.
- 14) This document, in part or in whole, may not be reprinted or reproduced without prior consent of ROHM



Thank you for your accessing to ROHM product informations. More detail product informations and catalogs are available, please contact us.

## ROHM Customer Support System

http://www.rohm.com/contact/

# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ROHM Semiconductor: UMH3NTN